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FGA3060ADF 600 V, 30 A Field Stop Trench IGBT

Features

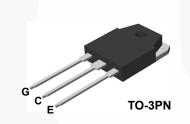
- Maximum Junction Temperature : T_J = 175°C
- Positive Temperaure Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: V_{CE(sat)} = 1.8 V(Typ.) @ I_C = 30 A
- + 100% of the Parts Tested for $I_{LM}(1)$
- High Input Impedance
- Fast Switching
- Tighten Parameter Distribution
- RoHS Compliant

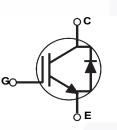
General Description

This ADF IGBT series adopted Field Stop Trench 3rd generation IGBT which offer extreme low Vce(sat) and much faster switching characteristics for outstanding efficiency. And this kind of technology is fully optimized to variety PFC (Power Factor Correction) topology ; Single boost, Multi channel interleaved etc with over 20KHz switching performance. TO3P package provide Super Low thermal resistance for much wider SOA for system stability.

Applications

 PFC topology for Home appliance : Single Boost , Multi channel Interleaved etc.





Absolute Maximum Ratings

Symbol	Description		FGA3060ADF	Unit
V _{CES}	Collector to Emitter Voltage		600	V
V	Gate to Emitter Voltage		± 20	V
V _{GES}	Transient Gate to Emitter Voltage		± 30	V
I _C	Collector Current	@ T _C = 25 ^o C	60	А
	Collector Current	@ T _C = 100°C	30	А
I _{LM (1)}	Pulsed Collector Current $@ T_C = 25^{\circ}C$		90	А
I _{CM (2)}	Pulsed Collector Current		90	А
I _{F (3)}	Diode Forward Current	@ T _C = 25°C	3	A
	Diode Forward Current	@ T _C = 100 ^o C	1.5	A
I _{FM (2)}	Pulsed Diode Maximum Forward Curr	rent	6	A
P _D	Maximum Power Dissipation	@ T _C = 25°C	176	W
. D	Maximum Power Dissipation	@ T _C = 100 ^o C	88	W
TJ	Operating Junction Temperature		-55 to +175	°C
T _{stg}	Storage Temperature Range		-55 to +175	°C
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes:

1. V_{CC} = 400 V, V_{GE} = 15 V, I_{C} = 90 A, R_{G} = 120 $\Omega,$ Inductive Load.

2. Repetitive rating: Pulse width limited by max. junction temperature.

3. The purpose of diode is protection for negative voltage.

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Thermal Characteristics

Symbol	Parameter	FGA3060ADF	Unit	
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case, Max.	0.85	°C/W	
$R_{\theta JC}$ (Diode)	Thermal Resistance, Junction to Case, Max.	5	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGA3060ADF	FGA3060ADF	TO-3PN	Tube	-	-	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	V _{GE} = 0 V, I _C = 1 mA	600	-	-	V
ΔBV_{CES} / ΔT_{J}	Temperature Coefficient of Breakdown Voltage	$I_{\rm C}$ = 1 mA, Reference to 25°C	-	0.52	-	V/ºC
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$	-	-	250	μA
I _{GES}	G-E Leakage Current	V_{GE} = V_{GES} , V_{CE} = 0 V	-	-	±400	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	I _C = 30 mA, V _{CE} = V _{GE}	4.1	5.6	7.6	V
- (- /		I _C = 30 A, V _{GE} = 15 V	-	1.8	2.3	V
V _{CE(sat)} Collector to Emitter Saturation Voltage		$I_{\rm C}$ = 30 A, $V_{\rm GE}$ = 15 V, $T_{\rm C}$ = 175°C	-	2.4	-	V
Dynamic C	haracteristics					
C _{ies}	Input Capacitance		-	1072	-	pF
C _{oes}	Output Capacitance	V _{CE} = 30 V, V _{GE} = 0 V, f = 1MHz	-	36	-	pF
C _{res}	Reverse Transfer Capacitance		-	13	-	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time		- 1	12	-	ns
t _r	Rise Time		-	19.2	-	ns
t _{d(off)}	Turn-Off Delay Time	V _{CC} = 400 V, I _C = 30 A,	-	42.4	-	ns
t _f	Fall Time	R _G = 6 Ω, V _{GE} = 15 V,	-	7.2	-	ns
Eon	Turn-On Switching Loss	Inductive Load, $T_C = 25^{\circ}C$	-	960		uJ
E _{off}	Turn-Off Switching Loss		-	165	-	uJ
E _{ts}	Total Switching Loss		-	1125	-	uJ
t _{d(on)}	Turn-On Delay Time		-	12.8	-	ns
t _r	Rise Time		-	27.2	-	ns
t _{d(off)}	Turn-Off Delay Time	V _{CC} = 400 V, I _C = 30 A,	-	46.4	-	ns
t _f	Fall Time	$R_G = 6 \Omega$, $V_{GE} = 15 V$,	-	12.8	-	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 175 ^o C	-	1430	-	uJ
E _{off}	Turn-Off Switching Loss		-	310	-	uJ
E _{ts}	Total Switching Loss		-	1740	-	uJ

Electrical Characteristics of the IGBT (Continued)

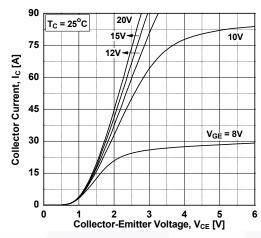
Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
Qg	Total Gate Charge		-	37.4	-	nC
Q _{ge}	Gate to Emitter Charge	V _{CE} = 400 V, I _C = 30 A, V _{GE} = 15 V	-	7.2	-	nC
Q _{gc}	Gate to Collector Charge	VGE - 10 V	-	15	-	nC

Electrical Characteristics of the Diode T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max	Unit
VEM	V _{FM} Diode Forward Voltage	I _F = 3 A	T _C = 25 ^o C	-	1.6	2.3	V
* FIVI			T _C = 175°C	-	1.4	-	
E _{rec}	Reverse Recovery Energy		T _C = 175 ^o C	-	29.7	-	uJ
t _{rr}	Diode Reverse Recovery Time	IX · · ·	$T_{\rm C} = 25^{\rm o}{\rm C}$	-	26	-	ns
T			T _C = 175°C	-	153	-	
0	Q _{rr} Diode Reverse Recovery Charge		T _C = 25 ^o C	-	35	-	nC
~			T _C = 175 ^o C	-	305	-	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics





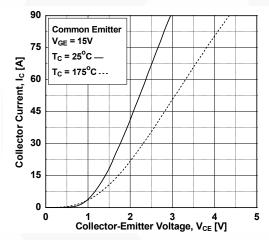


Figure 5. Saturation Voltage vs. V_{GE}

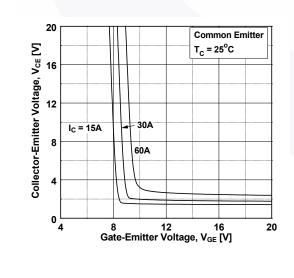
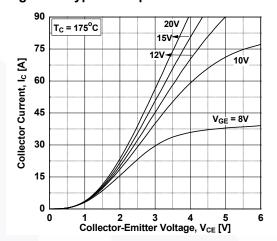
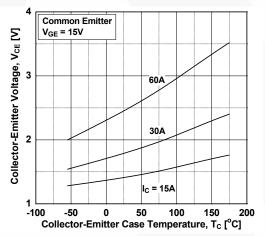


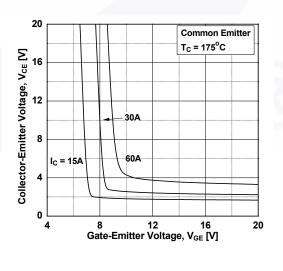
Figure 2. Typical Output Characteristics





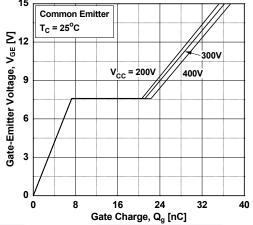




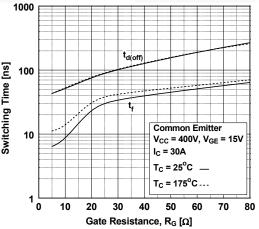


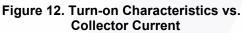
Typical Performance Characteristics Figure 7. Capacitance Characteristics 10000 15 Gate-Emitter Voltage, V_{GE} [V] 6 7 C_{ies} Capacitance [pF] 000 000 nes Common Emitter V_{GE} = 0V, f = 1MHz $T_C = 25^{\circ}C$ 0 10 0 10 30 Collector-Emitter Voltage, V_{CE} [V] Figure 9. Turn-on Characteristics vs. **Gate Resistance** 100 1000 Switching Time [ns] Switching Time [ns] 100 Common Emitter 10 V_{CC} = 400V, V_{GE} = 15V I_C = 30A 10 $T_C = 25^{\circ}C$ = 175°C Tc ¹0 5 0 10 20 30 40 50 60 70 80 Gate Resistance, R_G [Ω] Figure 11. Switching Loss vs. **Gate Resistance** 300 5000 100 Switching Time [ns] E Switching Loss [uJ] 1000 10 Common Emitter E V_{CC} = 400V, V_{GE} = 15V I_C = 30A $T_c = 25^{\circ}C$ 100 тс = 175°C 1 50 L 0 0 10 80 20 30 40 50 60 70 Gate Resistance, R_G [Ω]

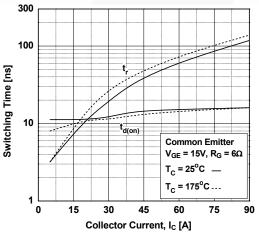
Figure 8. Gate charge Characteristics













Common Emitter

 $T_{c} = 25^{\circ}C$ _____

T_c = 175^oC ...

60

100µs

100

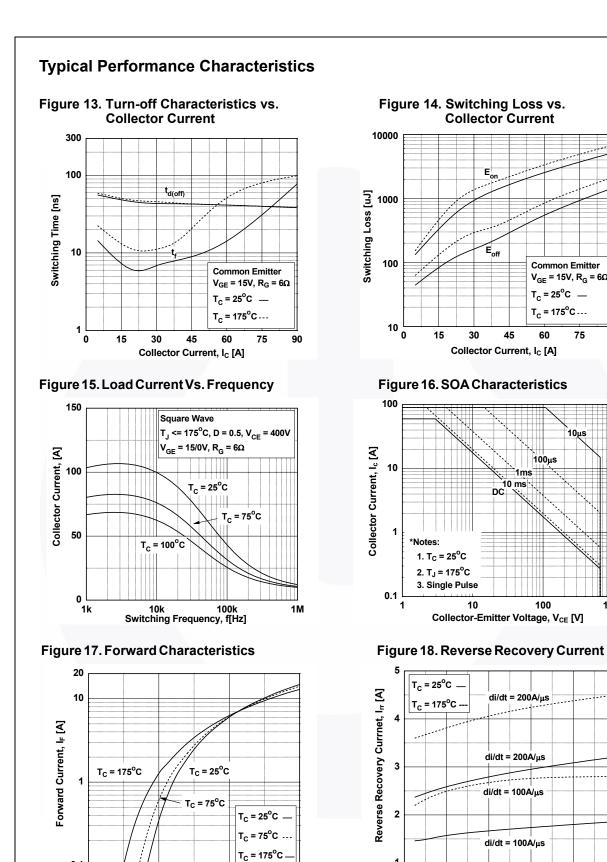
 V_{GE} = 15V, R_{G} = 6 Ω

75

10µs

90

1000



10

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1 2 Forward Voltage, V_F [V]

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3

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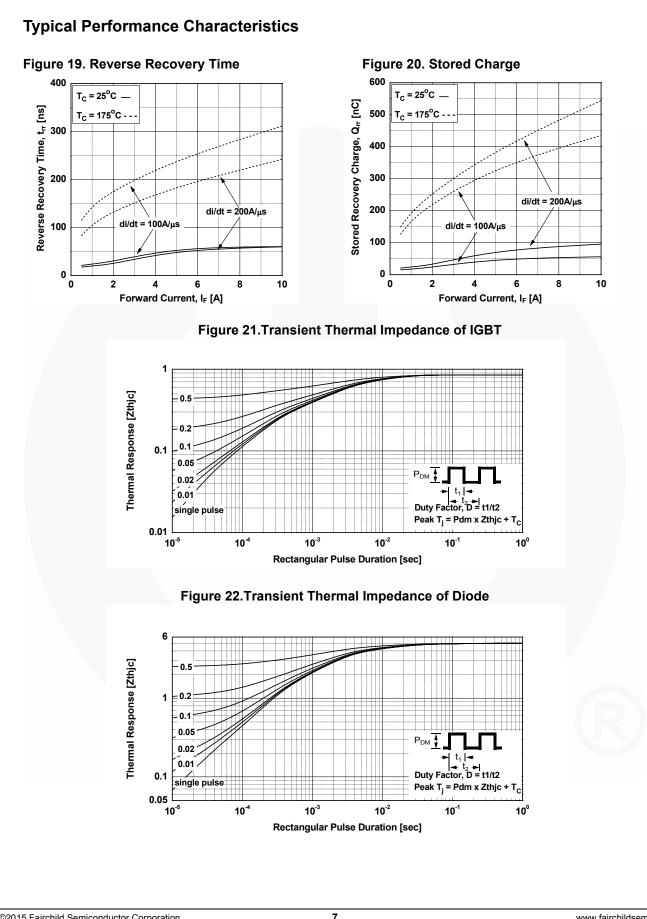
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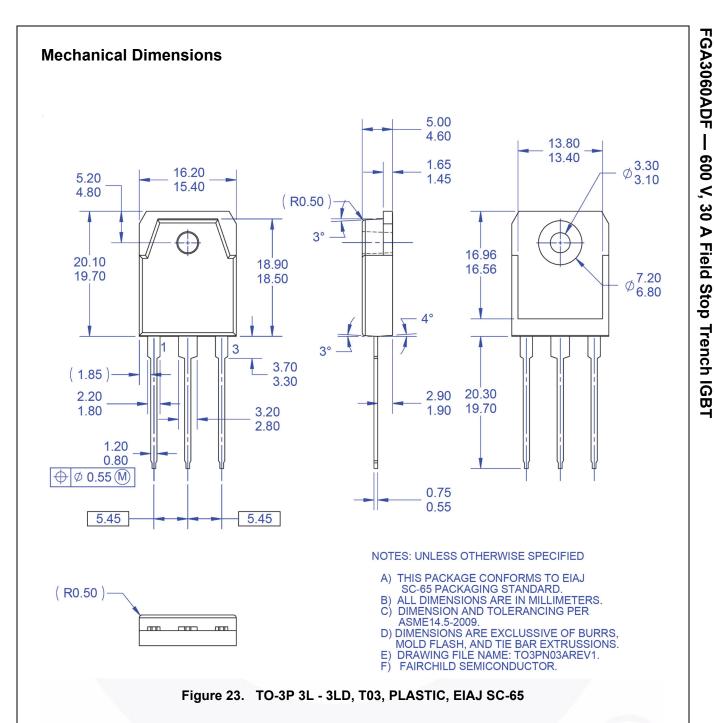
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Forward Current, I_F [A]

6

8





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